

| Ref # | Hits   | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|--------|---|---|------------------|---------|------------------|
| L26   | 158215 | (etch\$1 remov\$3) near5 (oxide dioxide barrier)                        | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 09:59 |
| L27   | 4988   | 26 same dielectric with (opening\$1 hole\$1 trench\$2 via\$1 recess\$2) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 10:00 |
| L28   | 158    | 27 same (silicon-near2 carbide SiC)                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 10:02 |

| Ref # | Hits   | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|--------|--|---|------------------|---------|------------------|
| L1    | 158215 | (etch\$1 remov\$3) near5 (oxide dioxide barrier)                       | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 13:12 |
| L2    | 4988   | 1 same dielectric with (opening\$1 hole\$1 trench\$2 via\$1 recess\$2) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 13:14 |
| L3    | 126    | 2 same ((poly amorphous) adj silicon refractory adj metal\$1)          | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 13:15 |
| L4    | 90     | 3 and (sidewall\$1 spacer\$1)  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2005/07/07 13:15 |